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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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**PATENT**

In re application of: Ni *et al.*

Application No.: 09/347,583

Filed: June 30, 1999

Title: MOVEABLE BARRIER FOR MULTIPLE ETCH PROCESSES



Attorney Docket No.:  
LAM1P111/P0513

Examiner: C. Brown

Group: 1765

**CERTIFICATE OF MAILING**  
I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail to: Assistant Commissioner for Patents, Washington, DC 20231 on February 27, 2001.

Signed: Natalie Morgan  
Natalie Morgan

**AMENDMENT**

Assistant Commissioner for Patents  
Box Amendment Fee  
Washington, D.C. 20231

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Sir:

This is in response to the Office Action mailed October, 11 2000.  
Reconsideration of the captioned application is respectfully requested.

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390.00 DP

**REMARKS**

Claims 1-13 have been rejected by the Examiner. Claims 1-13 are pending in this Application.

As mentioned on pages 1-3 of the Specification, the present invention relates to a diffusion barrier that can be positioned in multiple positions relative to the wafer. One known approach for improving etch rate uniformity in a chemically driven etch process is to install a diffusion barrier around the wafer perimeter. However, diffusion barriers are not used during ion-assisted (or ion-driven) etch processes (e.g. a plasma enhanced etch process). More specifically, the diffusion barrier is believed to quench the plasma and thus disturb the ion density uniformity in the plasma. If the barrier were to be used, the plasma density near the wafer perimeter would be lowered and thus cause a non-uniform etching during an ion assisted/driven etch. Because the